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In the Specification:

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Please amend the specification as follows:

Please replace the first paragraph on Page 3, starting at Line 1, with the following rewritten paragraph:

Please replace the last paragraph on Page 3, starting at Line 15 and extending to Page 4, with the following rewritten paragraph:

The gate of the transistor $\mathbb{M}2$ is connected to a reset terminal to receive the reset signal \mathbb{V}_{rst} . The sensor readout node \mathbb{FD} , that is the anode of the photo-diode \mathbb{D}_{F} , is first reset to a high voltage level (\mathbb{V}_{DD}) by changing the reset signal \mathbb{V}_{rst} from a low voltage level (0) to a high voltage level (\mathbb{V}_{DD}) to charge the capacitance \mathbb{C}_{FD} . At the completion of charging the capacitance \mathbb{C}_{FD} , the reset signal \mathbb{V}_{rst} is changed from the high voltage level (\mathbb{V}_{DD}) to the <u>low voltage level</u>. Since light is shown on the photo-diode \mathbb{D}_{F} , photo-generated electrons are collected at node \mathbb{FD} and the voltage at the node \mathbb{FD} decreases in the process. At the end of the exposure duration the voltage at node \mathbb{FD} is measured, thus completing one photo-sensing cycle. The photo-sensing cycle is completed by

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deactivating the transistor M3 by changing the row select signal from the high voltage level (V_{DD}) to the low voltage level (0).

Please replace the first paragraph on Page 6, starting at Line 10, with the following rewritten paragraph:

The voltage source VS1 driving the supply line V_{DD} 1 is set to a voltage level of the power supply voltage source V_{DD} source V_{DD} . A second voltage source connected to the V_{DD} 2 line is also set to the same value, the power supply voltage source V_{DD} source V_{DD} . Bright light is shown on the pixel so that it is saturated. The reset signal V_{rst} is pulsed periodically and the resulting average current from the voltage source is measured. The equation relating the measured average current I and the capacitance C_{FD} on the node FD of the photo-diode D_F is calculated by the formula:

Please replace the first paragraph on Page 29, starting at Line 4, with the following rewritten paragraph:

The operational mode for the testable APS cell of this invention is activated by closing switch \$1 to connect the voltage level V1 to the read distribution line \mathbb{RD} . During the normal operation, the voltage level V1 is set to the level of the power supply voltage source \mathbb{V}_{DD} source \mathbb{V}_{DD} . The testable APS pixel cell is reset by turning on the transistor M2 bringing the reset line \mathbb{V}_{rst} to a high level. The capacitance \mathbb{C}_{FD} is charged to the voltage level V1 which turns on the transistor M1. The row select signal \mathbb{V}_{row} is then activated and the reference

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level of the node \mathbb{FD} is sampled by the signal conditioning and readout circuit \mathbb{S} ig \mathbb{C}/\mathbb{R} as described above. The reset signal line \mathbb{V}_{rst} disables the transistor $\mathbb{M}2$. The light exposes the photodiode $\mathbb{D}_{\mathbb{F}}$ and as described above, electrons are collected at the node \mathbb{FD} . After an integration time, the signal conditioning and readout circuit \mathbb{S} ig \mathbb{C}/\mathbb{R} senses the collected charge of the node \mathbb{FD} , conditions the signals and provides the readout as also described above.

Please replace the first paragraph on Page 36, starting at Line 5, with the following rewritten paragraph:

The reference sample and hold signal SMR changes from the low voltage level (OV) to the high voltage level (V_{DD}) at the time \mathfrak{t}_7 to activate the signal conditioning and readout circuit Sig C/R to sample and retain the reference voltage level. The reference sample and hold signal SMR is changed from the high voltage level (V_{DD}) to the low voltage level (OV) at the time \mathfrak{t}_8 . The sensed signal output V_{sig_out} and the reference signal output V_{rst_out} are differentially compared to determine the voltage that is present at each node FD of each pixel. Since the voltage at each node FD of each pixel varies incrementially incrementally from the voltage level V2 to the voltage level V1, the output voltage of the signal conditioning and readout circuit Sig C/R will vary incrementially incrementally, dependent on the position of the connection of each to the resistor string R_1 , R_2 ,..., R_{n-1} , R_n . Since the values of the voltage level V1 and V2 are known, the linearity and functioning of the pixel and the int rmediate circuitry can be determined. Fig. 8 shows the results of testing a row of pixels as described

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above. As each pixel in the row is evaluated, the voltage level is recorded according to its position on the row. As is shown, the voltage level varies incrementally between zero volts and the difference between the voltage levels V1 and V2 depending on its position in the row and its connection location to the resistor string R_1 , R_2 ,..., R_{n-1} , R_n .